36V Operation 600mA Synchronous Step-Down DC/DC Converters

■GENERAL DESCRIPTION

The XC9267 series are 36V operation synchronous step-down DC/DC converter ICs with a built-in P-channel MOS driver transistor and N-channel MOS switching transistor.

The XC9267 series has operating voltage range of $3.0V \sim 36.0V$ and high-efficiency power supply up to an output current of 600mA. Low ESR capacitors such as ceramic capacitors can be used for the load capacitor (C_L).

A 0.75V reference voltage source is incorporated in the IC, and the output voltage can be set to a value from 1.0V to 25.0V using external resistors (R_{FB1}, R_{FB2}).

1.2MHz or 2.2MHz can be selected for the switching frequency.

The soft-start time is internally set to 2.0ms (TYP.), but can be adjusted to set a longer time using an external resistor and capacitor. With the built-in UVLO function, the driver transistor is forced OFF when input voltage becomes 2.7V or lower. The output state can be monitored using the power good function.

Internal protection circuits include over current protection and thermal shutdown circuits to enable safe use.

■ APPLICATIONS

- Electric Meter
- Gas Detector
- Various Sensor
- Industrial Equipment
- Home appliance

■ FEATURES

Input Voltage Range Output Voltage Range FB Voltage Oscillation Frequency Output Current Control Methods

Soft-start Time Protection Circuits

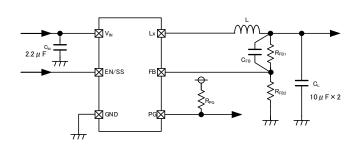
Output Capacitor Operating Ambient Temperature Packages

Environmentally Friendly

- 3.0 ~ 36V (Absolute Max 40V)
 1.0 ~ 25V
 0.75V±1.5%
 1.2MHz, 2.2MHz
 600mA
 PWM control Efficiency88%@12V→5V, 300mA
 Adjustable by RC
 Over Current Protection
 Thermal Shutdown
 Ceramic Capacitor
 - : 40°C ~ + 105°C
 - : SOT-89-5 (Without Power Good)
 - : USP-6C (With Power Good)
 - EU RoHS Compliant, Pb Free

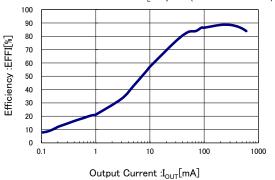
■ TYPICAL APPLICATION CIRCUIT

■ TYPICAL PERFORMANCE CHARACTERISTICS



XC9267B75Cxx (V_{IN}=12V, V_{OUT}=5V, f_{OSC}=1.2MHz)

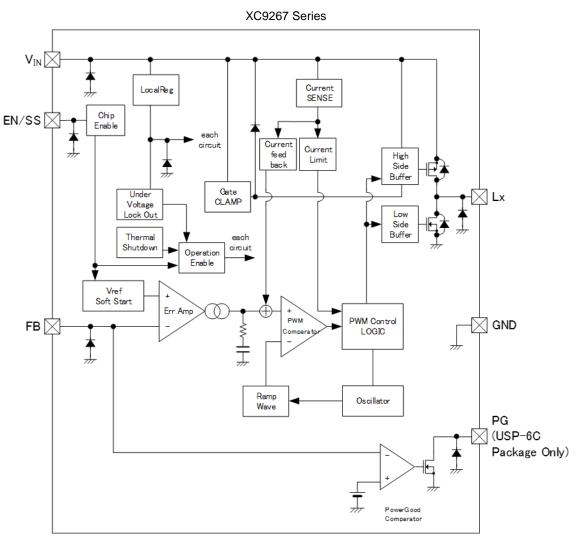
L=6.8 μ H(CLF5030NIT-6R8), C_{IN}=4.7 μ F×2(C2012X6S1H475K) C_L=10 μ F×2 (C3216X7R1E106K)



1/30

ETR05054-003

■ BLOCK DIAGRAM



Diodes inside the circuit are an ESD protection diodes and a parasitic diodes.

■ PRODUCT CLASSIFICATION

Ordering Information

XC9267(12)3(4)5(6)-(7)(*1) PWM control

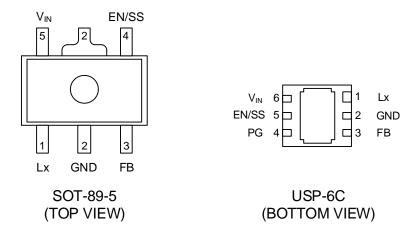
DESIGNATOR	ITEM	SYMBOL	DESCRIPTION
1	Turpo	В	Refer to Selection Guide
U	Туре	С	Refer to Selection Guide(Recommended products)
23	FB Voltage	75	0.75V
	Obsillation Fraguenay	С	1.2MHz
4	Oscillation Frequency	D	2.2MHz
	Deekease	PR-G ^(*1)	SOT-89-5 (1,000pcs/Reel)
56-7	Packages	ER-G ^(*1)	USP-6C (3,000pcs/Reel)

 $^{\scriptscriptstyle (*1)}$ The "-G" suffix denotes Halogen and Antimony free as well as being fully EU RoHS compliant.

Selection Guide

FUNCTION	B / C	TYPE
FUNCTION	SOT-89-5	USP-6C
Chip Enable	Yes	Yes
UVLO	Yes	Yes
Thermal Shutdown	Yes	Yes
Soft Start	Yes	Yes
Power-Good	-	Yes
Current Limitter (Automatic Recovery)	Yes	Yes

■ PIN CONFIGURATION



* The dissipation pad for the USP-6C package should be solder-plated in recommended mount pattern and metal masking so as to enhance mounting strength and heat release. If the pad needs to be connected to other pins, it should be connected to the GND (No. 2) pin.

■ PIN ASSIGNMENT

PIN NU	JMBER	PIN NAME	FUNCTION
SOT-89-5	USP-6C		FUNCTION
1	1	Lx	Switching Output
2	2	GND	Ground
3	3	FB	Output Voltage Sense
-	4	PG	Power-good Output
4	5	EN/SS	Enable Soft-start
5	6	VIN	Power Input

■ FUNCTION CHART

PIN NAME	SIGNAL	STATUS
	L	Stand-by
EN/SS	Н	Active
	OPEN	Undefined State ^(*1)

(¹) Please do not leave the EN/SS pin open. Each should have a certain voltage

PIN NAME	CON	IDITION	SIGNAL
	VFB > VPGDET		H (High impedance)
		$V_{FB} \leq V_{PGDET}$	L (Low impedance)
PG	EN/SS = H	Thermal Shutdown	L (Low impedance)
		UVLO (VIN < V _{UVL01})	Undefined State
	EN/SS = L	Stand-by	L (Low impedance)

■ABSOLUTE MAXIMUM RATINGS

PARAM	ETER	SYMBOL	RATINGS	UNITS
V _{IN} Pin V	oltage	Vin	-0.3 ~ 40	V
EN/SS Pin	Voltage	Ven/ss	-0.3 ~ 40	V
FB Pin V	oltage	Vfb	-0.3 ~ 6.2	V
PG Pin Vo	Itage ^(*1)	Vpg	-0.3 ~ 6.2	V
PG Pin C	urrent ^(*1)	IPG	8	mA
Lx Pin V	Lx Pin Voltage		-0.3 ~ V _{IN} + 0.3 or +40 ^(*2)	V
Lx Pin C	Lx Pin Current		1800	mA
Power Dissipation	SOT-89-5		1750 (JESD51-7 board) ^(*4)	mW
(Ta=25°C)	USP-6C	Pd	1250 (JESD51-7 board) ^(*4)	rnvv
Surge Ve	Surge Voltage		46 ^(*3)	V
Operating Ambier	Operating Ambient Temperature		-40 ~ 105	°C
Storage Ter	nperature	Tstg	-55 ~ 125	°C

* All voltages are described based on the GND pin.

(*1) For the USP-6C Package only.

 $^{(^{\ast}2)}$ The maximum value should be either V_IN+0.3V or 40V in the lowest.

 $^{(*3)}$ Applied Time ${\leq}400 ms$

(*4) The power dissipation figure shown is PCB mounted and is for reference only.

The mounting condition is please refer to PACKAGING INFORMATION.

ELECTRICAL CHARACTERISTICS

XC9267series

PARAMETER SYMBOL CONDITIONS MAX. UNIT CIRCUIT MIN. TYP. V_{FB}=0.739V→0.761V, FB Voltage VFBE VFB Voltage when Lx pin voltage 0.739 0.750 0.761 V 2 changes from"H" level to "L" level Setting Output VOUTSET 1 25 V _ Voltage Range (*1) **Operating Input** VIN 3 36 V Voltage Range (*1) $V_{EN/SS}=12V, V_{IN}:2.8V \rightarrow 2.6V, V_{FB}=0V$ 2 **UVLO Detect Voltage** VUVLOD VIN Voltage which Lx pin voltage 2.6 2.7 2.8 V holding "H" level V_{EN/SS}=12V,V_{IN}:2.7V→2.9V,V_{FB}=0V VIN Voltage which Lx pin voltage 2 **UVLO Release Voltage** VUVLOR 2.7 2.8 2.9 V holding "L" level fosc:1.2MHz 180 350 **(4)** Quiescent Current V_{FB}=0.825V μA lq fosc: 2.2MHz 290 500 -Stand-by Current VIN=12V, VEN/SS=VFB=0V **(4)** ISTBY 1.65 2.50 μA Connected to fosc: 1.2MHz 1.098 1.200 1.302 external **Oscillation Frequency** fosc MHz 1 components, 2.387 fosc: 2.2MHz 2.013 2.200 Iout=200mA 85 (*2) Minimum On Time tonmin Connected to external components ns 1 -Minimum Duty Cycle DMIN VFB=0.825V _ 0 % 2 Maximum Duty Cycle V_{FB}=0.675V 100 _ % 2 DMAX -5 Lx SW "H" On Resistance VFB=0.675V, ILx=200mA 1.20 RLxH -1.38 Ω 0.60 Lx SW "L" On Resistance R_{LxL} Ω (5) (*2) Highside Current Limit (*3) V_{FB}=V_{FBE}×0.98 1.30 А 5 1.00 **I**LIMH _ Internal Soft-Start Time VFB=0.675V 1.6 2.0 2.4 2 tss1 ms VFB=0.675V External Soft-Start Time 21 26 33 3 tss2 ms Rss=430KΩ, Css=0.47µF V_{FB}=0.712V→0.638V, R_{PG}:100kΩ pull-up to 5V (5) PG detect voltage (*4) VPGDET 0.638 0.675 0.712 V VFB Voltage when PG pin voltage changes from"H" level to "L" level PG Output voltage (*4) V 2 V_{PG} VFB=0.6V, IPG=1mA 0.3 -_ Connected to external components, 1 Efficiency (*5) EFFI 88 % _ VIN=12V, VOUT=5V, IOUT=300mA FB Voltage $\Delta V_{FB}/$ 2 Temperature -40°C≦T_{opr}≦105°C ±100 ppm/°C _ (ΔT_{opr}·V_{FBE}) Characteristics

Ta=25°C

Test Condition: Unless otherwise stated, V_{IN} =12V, $V_{EN/SS}$ =12V, V_{PG} :OPEN (*4)

Peripheral parts connection conditions :

 $L=6.8\mu H, R_{FB1}=680k\Omega, R_{FB2}=120k\Omega, C_{FB}=18pF, C_L=10\mu F\times 2parallel, C_{IN}=2.2\mu F, C_L=10\mu F,$

^(*1) Please use within the range of $V_{OUT}/V_{IN} \ge t_{ONMIN}[ns] \times f_{OSC}[MHz] \times 10^{-3}$

^(*2) Design reference value. This parameter is provided only for reference.

^(*3) Current limit denotes the level of detection at peak of coil current.

(*4) For the USP-6C Package only.

(*5) EFFI = {(output voltage) x (output current)} / {(input voltage) x (input current)} x 100

ELECTRICAL CHARACTERISTICS(Continued)

XC9267 series

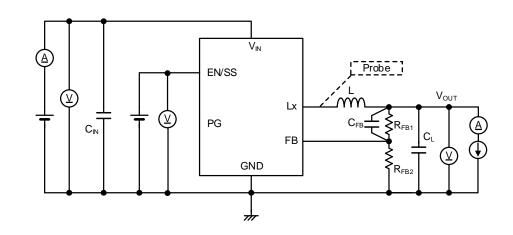
XC9267 series						Ta=2	25°C
ARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT	CIRCUIT
FB "H" Current	IFBH	VIN=VEN/SS=36V, VFB=3.0V	-0.1	-	0.1	μA	4
FB "L" Current	I _{FBL}	$V_{IN}=V_{EN/SS}=36V, V_{FB}=0V$	-0.1	-	0.1	μA	4
EN/SS "H" Voltage	Ven/ssh	$V_{EN/SS}=0.3V \rightarrow 2.5V$, $V_{FB}=0.71V$ $V_{EN/SS}$ Voltage when Lx pin voltage changes from "L" level to "H" level	2.5	-	36	V	2
EN/SS "L" Voltage	Ven/ssl	$V_{EN/SS}=2.5V\rightarrow0.3V$, $V_{FB}=0.71V$ $V_{EN/SS}$ Voltage when Lx pin voltage changes from "H" level to "L" level	-	-	0.3	V	2
EN/SS "H" Current	I _{EN/SSH}	VIN=VEN/SS=36V, VFB=0.825V	-	0.1	0.3	μA	4
EN/SS "L" Current	I _{EN/SSL}	VIN=36V, VEN/SS=0V, VFB=0.825V	-0.1	-	0.1	μA	4
Thermal Shutdown Temperature	T _{TSD}	Junction Temperature	-	150	-	°C	_
Hysteresis Width	T _{HYS}	Junction Temperature	-	25	-	°C	-

Test Condition: Unless otherwise stated, V_{IN}=12V, V_{EN/SS}=12V, V_{PG}:OPEN (*4)

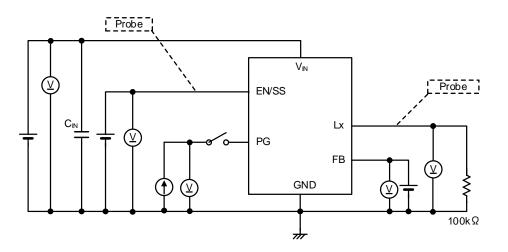
(*4) For the USP-6C Package only.

■TEST CIRCUITS

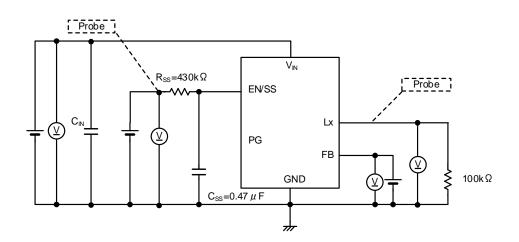
CIRCUIT



CIRCUIT2



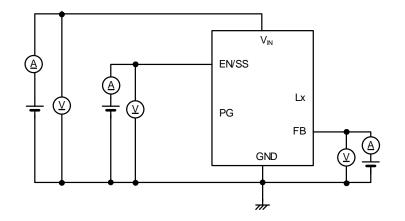
CIRCUIT(3)



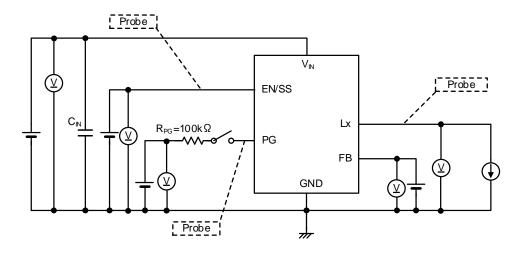
* PG Pin is USP-6C Package only.

■TEST CIRCUITS(Continued)

CIRCUIT(4)

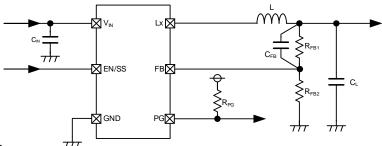


CIRCUIT(5)



* PG Pin is USP-6C Package only.

■TYPICAL APPLICATION CIRCUIT



<Inductance value setting>

For the XC9267 Series, operation is optimized by setting the following inductance value according to the set frequency and setting output voltage.

foscset: Frequency setting , VOUTSET: Output voltage setting [Typical Examples]

	f _{oscset}	conditions	MANUFACTURER	PRODUCT NUMBER	VALUE			
			TDK	CLF5030NIT-3R3N				
			Coilcraft	XEL4030-332ME				
		1V <v<sub>OUTSET≦2V</v<sub>	Taiyo Yuden	NRS4018T3R3MDGJ	3.3µН			
			Tokyo Coil	SHP0420P-F3R3NAP				
			TDK	CLF5030NIT-4R7N				
			Coilcraft	XEL4030-472ME	(-			
		2V <v<sub>OUTSET≦3.3V</v<sub>	Taiyo Yuden	NRS5024T4R7MMGJ	4.7µH			
	1 2MHz		Tokyo Coil	SHP0530P-F4R7AP				
	1.2MHz		TDK	CLF5030NIT-6R8N				
		3.3V <v<sub>OUTSET≦6V</v<sub>	Coilcraft	XEL4030-682ME	6.8µH			
			Taiyo Yuden	NRS5024T6R8MMGJ				
			Tokyo Coil	SHP0530P-F6R8AP				
			TDK	CLF5030NIT-100N				
		6V <v<sub>OUTSET≦25V</v<sub>	Taiyo Yuden	NRS5040T100MMGJ	10µH			
L			Tokyo Coil	SHP0530P-F100AP				
		1V <v<sub>outset≦2V</v<sub>	TDK	CLF5030NIT-1R5N	1.5µH			
			Coilcraft	XEL4030-152ME				
			Taiyo Yuden	NRS4018T1R5NDGJ				
			Tokyo Coil	SHP0420P-F1R6NAP	1.6µH			
			TDK	CLF5030NIT-2R2N				
		2V <v<sub>OUTSET≦3.3V</v<sub>	Coilcraft	XEL4030-222ME	2.2µН 3.3µН			
			Taiyo Yuden	NRS4018T2R2MDGJ				
	0.00411-		Tokyo Coil	SHP0420P-F2R2NAP				
	2.2MHz		TDK	CLF5030NIT-3R3N				
			Coilcraft	XEL4030-332ME				
		3.3V <v<sub>OUTSET≦6V</v<sub>	Taiyo Yuden	NRS4018T3R3MDGJ				
			Tokyo Coil	SHP0420P-F3R3NAP				
			TDK	CLF5030NIT-4R7N				
			Coilcraft	XEL4030-472ME	. –			
		6V <v<sub>OUTSET≦25V</v<sub>	Taiyo Yuden	NRS5024T4R7MMGJ	4.7µH			
			Tokyo Coil	SHP0530P-F4R7AP				
		V _{IN} <20V	TDK	C2012X6S1H475K125AC	4.7µF/50V			
•	1.2MHz	V _{IN} ≧20V	TDK	C2012X6S1H475K125AC	4.7µF/50V 2parallel			
CIN	0.01/1-	V _{IN} <20V	TDK	C2012X7R1H225K125AC	2.2µF/50V			
	2.2MHz	V _{IN} ≧20V	TDK	C2012X7R1H225K125AC	2.2µF/50V 2parallel			
	Ī			C2012X7R1A106K125AC	10µF/10V 2parallel			
C_{L}	-	-	TDK	C3216X7R1E106K160AB	10µF/25V 2parallel			
				C3225X7R1H106M250AC	10µF/50V 2parallel			

■TYPICAL APPLICATION CIRCUIT(Continued)

< Output voltage setting >

The output voltage can be set by adding an external dividing resistor.

The output voltage is determined by the equation below based on the values of RFB1 and RFB2.

 $V_{\text{OUT}}{=}0.75V \times (R_{\text{FB1}}{+}R_{\text{FB2}})/R_{\text{FB2}}$ With RFB2 ${\leq}200k\Omega$ and RFB1+RFB2 ${\leq}1M\Omega$

<CFB setting>

Adjust the value of the phase compensation speed-up capacitor CFB using the equation below.

$$C_{FB} = \frac{1}{2\pi \times fz fb \times R_{FB1}}$$

A target value for fzfb of about $fzfb = \frac{1}{2\pi\sqrt{C_L \times L}}$ is optimum.

[Setting Example]

To set output voltage to 5V with fosc=1.2MHz, CL=10 μ Fx2, L=6.8 μ H

When R_{FB1} =680k Ω , R_{FB2} =120k Ω , V_{OUTSET} =0.75V× (680k Ω +120k Ω) / 120k Ω =5.0V And fzfb is set to a target of 13.65 kHz using the above equation, C_{FB} =1/ (2× π ×13.65 kHz×680k Ω) =17.15pF. A capacitor of E24 series is 18pF.

	f _{OSC} =1.2MHz						fosc=2.	2MHz			
VOUTSET	R _{FB1}	R _{FB2}	L	Сгв	fzfb	VOUTSET	R _{FB1}	R _{FB2}	L	CFB	fzfb
1.2V	120kΩ	200kΩ	3.3µH	68pF	19.6kHz	1.2V	120kΩ	200kΩ	1.5µH	47pF	29.1kHz
3.3V	510kΩ	150kΩ	4.7µH	18pF	16.4kHz	3.3V	510kΩ	150kΩ	2.2µH	12pF	24.0kHz
5.0V	680kΩ	120kΩ	6.8µH	18pF	13.7kHz	5.0V	680kΩ	120kΩ	3.3µH	12pF	19.6kHz
12V	360kΩ	24kΩ	10µH	39pF	11.3kHz	12V	360kΩ	24kΩ	4.7µH	27pF	16.4kHz

<Soft-start Time Setting>

The soft-start time can be adjusted by adding a capacitor and a resistor to the EN/SS pin. Soft-start time (tss2) is approximated by the equation below according to values of V_{EN/SS}, Rss, and Css.

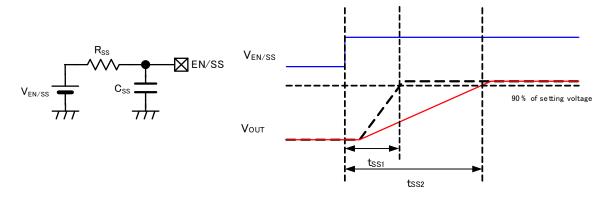
 $t_{ss2}=C_{ss} \times R_{ss} \times \ln (V_{EN/SS} / (V_{EN/SS} - 1.45))$

[Setting Example]

When C_{SS}=0.47μF, R_{SS}=430kΩ and V_{EN/SS}=12V, t_{SS2}=0.47x10⁻⁶ x 430 x 10³ x (ln (12/ (12-1.45)) =26ms (Approx.)

*The soft-start time is the time from the start of VEN/SS until the output voltage reaches 90% of the set voltage.

If the EN/SS pin voltage rises steeply without connecting C_{SS} and R_{SS} (R_{SS}= 0Ω), Output rises with taking the soft-start time of t_{SS1}=2.0ms (TYP.) which is fixed internally.

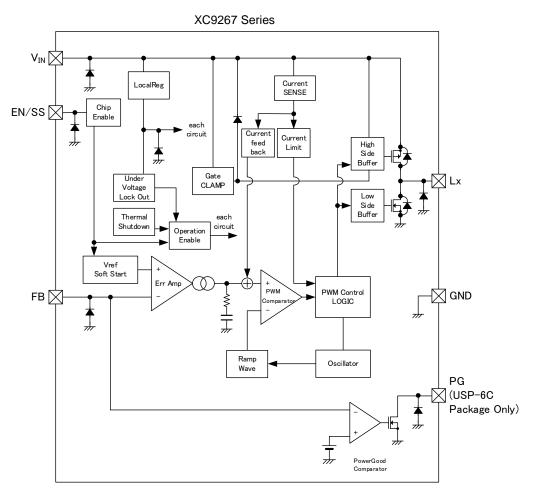


■OPERATIONAL EXPLANATION

The XC9267 series consists internally of a reference voltage supply with soft-start function, error amp, PWM comparator, ramp wave circuit, oscillator circuit, phase compensation (Current feedback) circuit, current limiting circuit, current limit PFM circuit, High-side driver Tr., Low-side driver Tr., buffer drive circuit, internal power supply (LocalReg) circuit, under-voltage lockout (UVLO) circuit, gate clamp (CLAMP) circuit, thermal shutdown (TSD) circuit, power good comparator, PWM control block and other elements.

The voltage feedback from the FB pin is compared to the internal reference voltage by the error amp, the output from the error amp is phase compensated, and the signal is input to the PWM comparator to determine the ON time of switching during PWM operation. The output signal from the error amp is compared to the ramp wave by the PWM comparator, and the output is sent to the buffer drive circuit and output from the LX pin as the duty width of switching. This operation is performed continuously to stabilize the output voltage.

The driver transistor current is monitored at each switching by the phase compensation (Current feedback) circuit, and the output signal from the error amp is modulated as a multi-feedback signal. This allows a stable feedback system to be obtained even when a low ESR capacitor such as a ceramic capacitor is used, and this stabilizes the output voltage.



* Diodes inside the circuits are ESD protection diodes and parasitic diodes.

<Reference voltage source>

The reference voltage source provides the reference voltage to ensure stable output voltage of the DC/DC converter.

<Oscillator circuit>

The oscillator circuit determines switching frequency.1.2MHz or 2.2MHz is available for the switching frequency. Clock pulses generated in this circuit are used to produce ramp waveforms needed for PWM operation.

<Error amplifier>

The error amplifier is designed to monitor output voltage. The amplifier compares the reference voltage with the feedback voltage divided by the internal voltage divider, R_{FB1} and R_{FB2}. When a voltage is lower than the reference voltage, then the voltage is fed back, the output voltage of the error amplifier increases. The error amplifier output is fixed internally to deliver an optimized signal to the mixer.

■ OPERATIONAL EXPLANATION(Continued)

<Current limiting>

The current limiting circuit of the XC9267 series monitors the current that flows through the High-side driver transistor and Low-side driver transistor, and when over-current is detected, the current limiting function activates.

(1) High-side driver Tr. current limiting

The current in the High-side driver Tr. is detected to equivalently monitor the peak value of the coil current. The High-side driver Tr. current limiting function forcibly turns off the High-side driver Tr. when the peak value of the coil current reaches the High-side driver current limit value ILIMH.

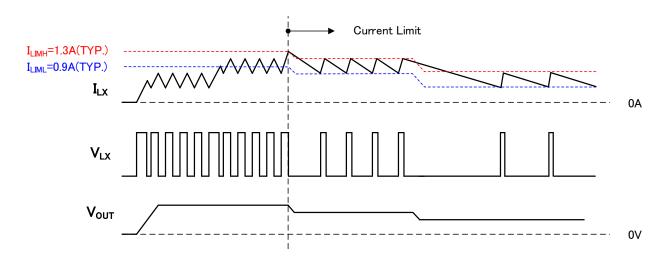
High-side driver Tr. current limit value ILIMH=1.3A (TYP.)

(2) Low-side driver Tr. current limiting

The current in the Low-side driver Tr. is detected to equivalently monitor the bottom value of the coil current. The Low-side driver Tr. current limiting function operates when the High-side driver Tr. current limiting value reaches I_{LIMH}. The Low-side driver Tr. current limiting function prohibits the High-side driver Tr. from turning on in an over-current state where the bottom value of the coil current is higher than the Low-side driver Tr. current limit value I_{LIML}.

Low side driver Tr. current limit value ILIML=0.9A (TYP.)

The current foldback circuit operates control to lower the switching frequency fosc. When the over-current state is released, normal operation resumes.



■ OPERATIONAL EXPLANATION(Continued)

<Soft-start function>

The output voltage of XC9267 rises with soft start by slowly raising the reference voltage. The rise time of this reference voltage is the soft start time. The soft-start time is set to t_{ss1} (TYP. 2.0ms) which is fixed internally or to the time set by adding a capacitor and a resistor to the EN / SS pin whichever is later.

<Thermal shutdown>

The thermal shutdown (TSD) as an over temperature limit is built in the XC9267 series.

When the junction temperature reaches the detection temperature, the driver transistor is forcibly turned off. When the junction temperature falls to the release temperature while in the output stop state, restart takes place by soft-start.

<UVLO>

When the V_{IN} pin voltage falls below V_{UVLO1} (TYP. 2.7V), the driver transistor is forcibly turned off to prevent false pulse output due to instable operation of the internal circuits. When the V_{IN} pin voltage rises above V_{UVLO2} (TYP. 2.8V), the UVLO function is released, the soft-start function activates, and output start operation begins. Stopping by UVLO is not shutdown; only pulse output is stopped and the internal circuits continue to operate.

<Power good>

On USP-6C Package, the output state can be monitored using the power good function. The PG pin is an Nch open drain output, therefore a pull-up resistance (approx. $100k\Omega$) must be connected to the PG pin.

	CONDITIONS	SIGNAL
	$V_{FB} > V_{PGDET}$	H (High impedance)
	$V_{FB} \leq V_{PGDET}$	L (Low impedance)
EN/SS=H	Thermal Shutdown	L (Low impedance)
	UVLO	Undefined State
	$(V_{IN} < V_{UVLO1})$	Ondenned State
EN/SS=L	Stand-by	L (Low impedance)

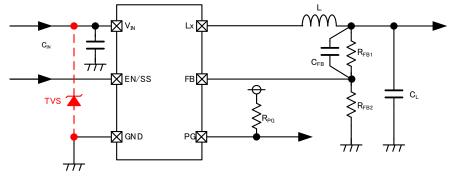
■NOTE ON USE

1) In the case of a temporary and transient voltage drop or voltage rise.

If the absolute maximum ratings are exceeded, the IC may be deteriorate or destroyed.

Case 1

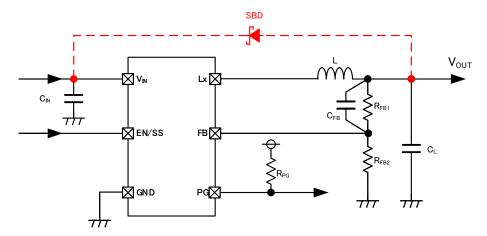
If a voltage exceeding the absolute maximum rating is applied to this IC due to chattering by a mechanical switch or an external surge voltage, etc., take measures using a protection circuit such as TVS.



Case 2

Under conditions where the input voltage is less than the output setting voltage, the absolute maximum rating of the Lx pin may be exceeded, and an overcurrent may flow in the parasitic diode inside the IC.

If excessive current flows in the parasitic diode, take measures such as adding the SBD between VOUT and VIN.



2) Make sure that the absolute maximum ratings of the external components and of this IC are not exceeded.

3) The DC/DC converter characteristics depend greatly on the externally connected components as well as on the characteristics of this IC, so refer to the specifications and standard circuit examples of each component when carefully considering which components to select.

Be especially careful of the capacitor characteristics and use X7R or X5R (EIA standard) ceramic capacitors. The capacitance decrease caused by the bias voltage may become remarkable depending on the external size of the capacitor.

4) The DC/DC converter of this IC uses a current-limiting circuit to monitor the coil peak current. If the potential dropout voltage is large or the load current is large, the peak current will increase, which makes it easier for current limitation to be applied which in turn could cause the operation to become unstable. When the peak current becomes large, adjust the coil inductance and sufficiently check the operation.

The following formula is used to show the peak current. Peak Current: $Ipk = (V_{IN} - V_{OUT}) \times V_{OUT} / V_{IN} / (2 \times L \times f_{OSC}) + I_{OUT}$

L: Coil Inductance [H] fosc: Oscillation Frequency [Hz] I_{OUT}: Load Current [A]

- 5) If there is a large dropout voltage, a circuit delay could create the ramp-up of coil current with staircase waveform exceeding the current limit.
- 6) Even in the PWM control, the intermittent operation occurs and the ripple voltage becomes higher, when the minimum On Time is faster than 85ns (typ.) as well as the dropout voltage is large and output current is small.

TOREX 15/30

■NOTE ON USE(Continued)

- 7) The ripple voltage could be increased when switching from discontinuous conduction mode to continuous conduction mode and at switching to 100% Duty cycle. Please evaluate IC well on customer's PCB.
- 8) If the voltage at the EN/SS Pin does not start from 0V but it is at the midpoint potential when the power is switched on, the soft start function may not work properly and it may cause the larger inrush current and bigger ripple voltages.
- 9) Torex places an importance on improving our products and their reliability. We request that users incorporate fail-safe designs and post-aging protection treatment when using Torex products in their systems.
- 10) Instructions of pattern layouts

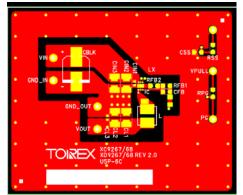
The operation may become unstable due to noise and/or phase lag from the output current when the wire impedance is high, please place the input capacitor(C_{IN}) and the output capacitor (C_L) as close to the IC as possible.

- (1) In order to stabilize V_{IN} voltage level, we recommend that a by-pass capacitor (C_{IN}) be connected as close as possible to the V_{IN} and GND pins.
- (2) Please mount each external component as close to the IC as possible.
- (3) Wire external components as close to the IC as possible and use thick, short connecting traces to reduce the circuit impedance.
- (4) Make sure that the GND traces are as thick as possible, as variations in ground potential caused by high ground currents at the time of switching may result in instability of the IC.
- (5) Please note that internal driver transistors bring on heat because of the load current and ON resistance of Highside driver transistor. Lowside driver transistor. Please make sure that the heat is dissipated properly, especially at higher temperatures.

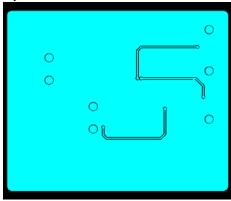
<Reference Pattern Layout>

USP-6C

Layer 1

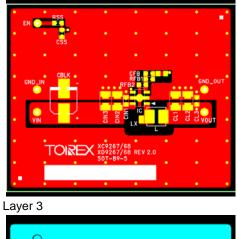


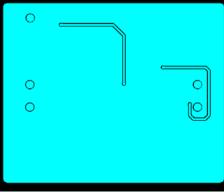
Layer 3



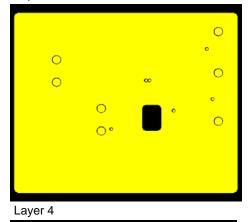
<u>SOT-89-5</u>

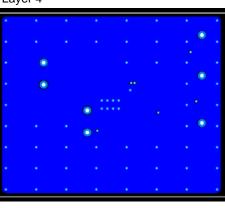
Layer 1

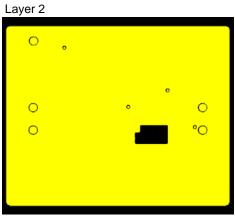




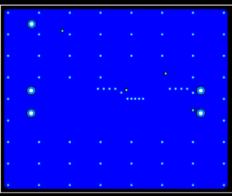
Layer 2





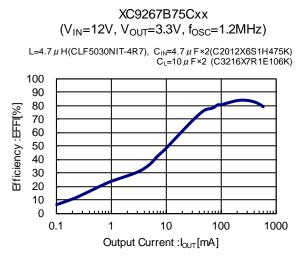


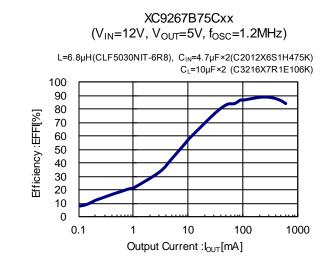
Layer 4



■TYPICAL PERFORMANCE CHARACTERISTICS

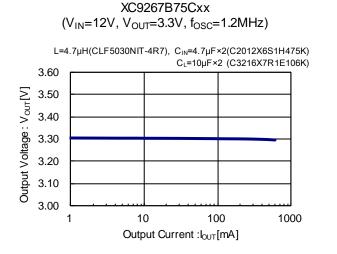
(1) Efficiency vs. Output Current

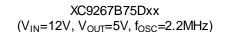


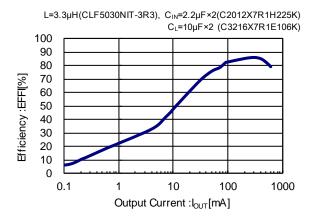


XC9267B75Dxx (V_{IN}=12V, V_{OUT}=3.3V, f_{OSC}=2.2MHz) L=2.2µH(CLF5030NIT-2R2), C_{IN}=2.2µF×2(C2012X7R1H225K) CL=10µF × 2 (C3216X7R1E106K) 100 90 80 Efficiency : EFFI[%] 70 60 50 40 30 20 10 0 0.1 10 100 1000 1 Output Current : IOUT [mA]

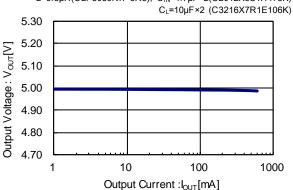
(2) Output Voltage vs. Output Current





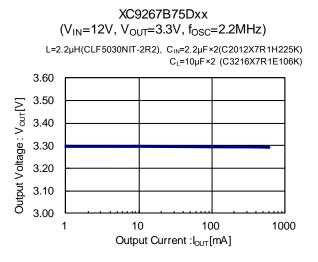


XC9267B75Cxx (V_{IN}=12V, V_{OUT}=5V, f_{OSC}=1.2MHz)

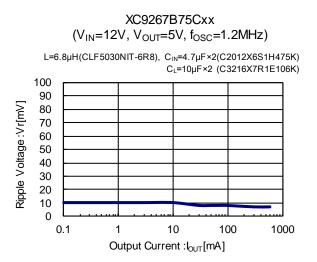


L=6.8µH(CLF5030NIT-6R8), C_{IN}=4.7µF×2(C2012X6S1H475K) C_{II}=10µF×2 (C3216X7R1E106K)

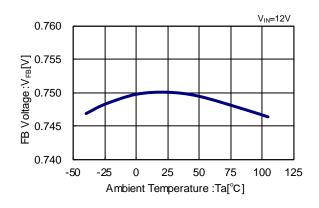
(2) Output Voltage vs. Output Current



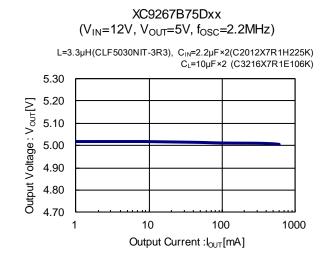
(3) Ripple Voltage vs. Output Current



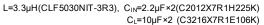
(4) FB Voltage vs. Ambient Temperature

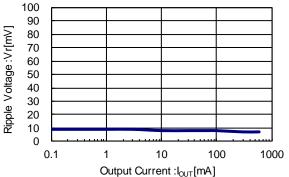


XC9267B75xxx



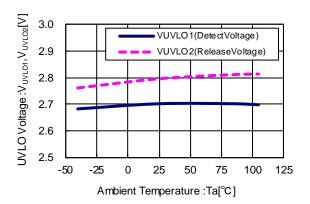
XC9267B75Dxx (V_{IN} =12V, V_{OUT} =5V, f_{OSC} =2.2MHz)





(5) UVLO Voltage vs. Ambient Temperature

XC9267B75xxx

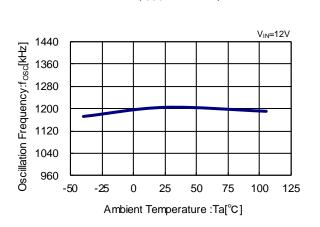


■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

(6) Oscillation Frequency vs. Ambient Temperature

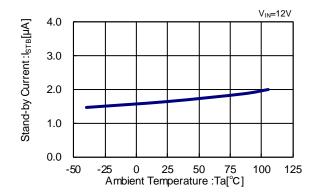
XC9267B75Cxx

(f_{OSC}=1.2MHz)



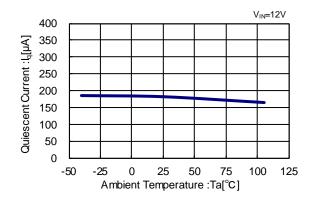
(7) Stand-by Current vs. Ambient Temperature

XC9267B75xxx

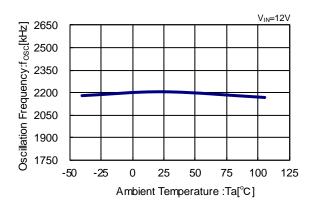


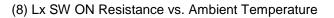
(9) Quiescent Current vs. Ambient Temperature



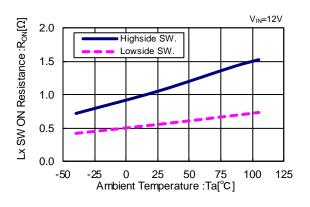


XC9267B75Dxx (f_{OSC}=2.2MHz)

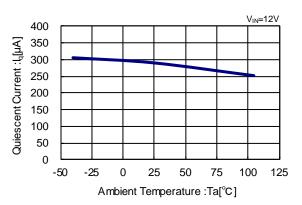




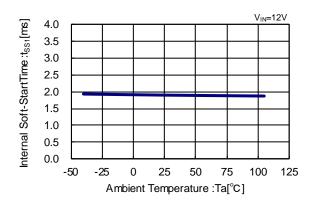
XC9267B75xxx



XC9267B75Dxx (f_{OSC}=2.2MHz)

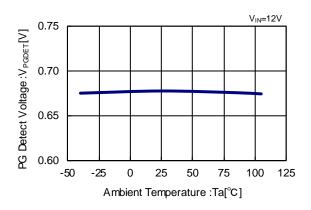


XC9267B75xxx

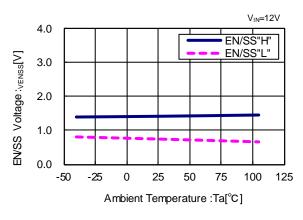


(12) PG Detect Voltage vs. Ambient Temperature

XC9267B75xxx



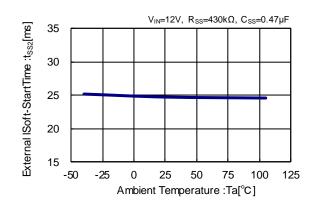
(14) EN/SS Voltage vs. Ambient Temperature





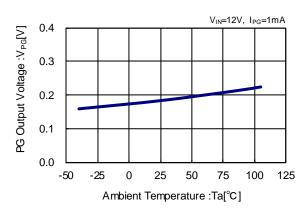
(10) Internal Soft-Start Time vs. Ambient Temperature (11) External Soft-Start Time vs. Ambient Temperature

XC9267B75xxx



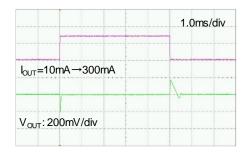
(13) PG Output Voltage vs. Ambient Temperature

XC9267B75xxx

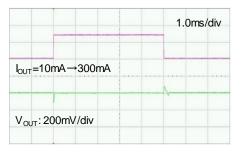


(15) Load Transient Response

 $\begin{array}{l} XC9267B75Cxx, \ f_{OSC} = 1.2MHz \\ V_{IN} = 12V, \ V_{OUT} = 3.3V, \ I_{OUT} = 10mA \rightarrow 300mA \\ L = 4.7 \mu H (CLF5030NIT - 4R7), \ C_{IN} = 4.7 \mu F \times 2 (C2012X6S1H475K) \\ C_{L} = 10 \mu F \times 2 \ (C3216X7R1E106K) \end{array}$



$\begin{array}{l} XC9267B75Cxx, \ f_{OSC} = 1.2MHz \\ v_{\text{IN}} = 24V, \ v_{\text{OUT}} = 3.3V, \ I_{\text{OUT}} = 10\text{mA} \rightarrow 300\text{mA} \\ \text{L} = 4.7 \mu\text{H}(\text{CLF5030NIT-4R7}), \ C_{\text{IN}} = 4.7 \mu\text{F} \times 2(\text{C2012X6S1H475K}) \\ C_{\text{L}} = 10 \mu\text{F} \times 2 \ (\text{C3216X7R1E106K}) \end{array}$



XC9267B75Cxx, f_{OSC} =1.2MHz

 V_{IN} =12V, V_{OUT} =5.0V, I_{OUT} =10mA→300mA L=6.8µH(CLF5030NIT-6R8), C_{IN} =4.7µF×2(C2012X6S1H475K)

 $C_{L}=10\mu F \times 2 (C_{2}U12X6S1H475K)$ $C_{L}=10\mu F \times 2 (C_{2}U12X6S1H475K)$

	1.0ms/div
l _{ouτ} =10mA→300mA	
V _{our} : 200mV/div	V

XC9267B75Cxx, f_{OSC} =1.2MHz

 $\label{eq:VINE24V, V_{OUT}=5.0V, I_{OUT}=10mA \rightarrow 300mA \\ L=6.8 \mu H (CLF5030NIT-6R8), \ C_{IN}=4.7 \mu F \times 2 (C2012X6S1H475K) \\ C_{L}=10 \mu F \times 2 \ (C3216X7R1E106K) \\ \end{array}$

······	1.0ms/div
l _{ou⊤} =10mA→300mA	
V _{OUT} : 200mV/div	

XC9267B75Dxx, f_{OSC} =2.2MHz

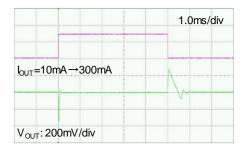
 $V_{\text{IN}}\text{=}12\text{V}, \ V_{\text{OUT}}\text{=}3.3\text{V}, \ I_{\text{OUT}}\text{=}10\text{mA}{\rightarrow}300\text{mA}$

 $\label{eq:L22} \begin{array}{l} L=\!2.2 \mu H(CLF5030NIT\mathcal{IT}\mathcal{I}\mbox{2}), \ C_{IN}\!=\!2.2 \mu F\mbox{2}(C2012X7R1H225K) \\ C_{L}\!=\!10 \mu F\mbox{2} (C3216X7R1E106K) \end{array}$

	1.0ms/div
l _{ou⊤} =10mA→300mA	
V _{out} : 200mV/div	

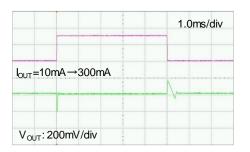
(15) Load Transient Response

 $\begin{array}{l} XC9267B75Dxx, \ f_{OSC}{=}2.2MHz \\ V_{IN}{=}12V, \ V_{OUT}{=}5.0V, \ I_{OUT}{=}10mA{\rightarrow}300mA \\ L{=}3.3\mu H(CLF5030NIT{-}3R3), \ C_{IN}{=}2.2\mu F{\times}2(C2012X7R1H225K) \\ C_{L}{=}10\mu F{\times}2 \ (C3216X7R1E106K) \end{array}$



16) Input Transient Beenenee

 $\begin{array}{l} XC9267B75Dxx, \ f_{OSC}=\!2.2MHz \\ V_{IN}\!=\!24V, \ V_{OUT}\!=\!5.0V, \ I_{OUT}\!=\!10mA\!\rightarrow\!300mA \\ L\!=\!3.3\mu H(CLF5030NIT\!-\!3R3), \ C_{IN}\!=\!2.2\mu F\!\times\!2(C2012X7R1H225K) \\ C_L\!=\!10\mu F\!\times\!2 \ (C3216X7R1E106K) \end{array}$



(16) Input Transient Response

XC9267B75Cxx, f_{OSC}=1.2MHz V_{IN}=8V→16V, V_{OUT}=3.3V, I_{OUT}=300mA L=4.7µH(CLF5030NIT-4R7), C_{IN}=4.7µF×2(C2012X6S1H475K) C_L=10µF×2 (C3216X7R1E106K)

	1.0ms/div
V _{IN} =8V→16V	
V _{out} : 200mV/div	V

XC9267B75Cxx、f_{OSC}=1.2MHz

$$\label{eq:VIN=16V} \begin{split} V_{\text{IN}} = 16V &\rightarrow 32V, \ V_{\text{OUT}} = 3.3V, \ I_{\text{OUT}} = 3.00\text{mA} \\ \text{L} = 4.7 \mu \text{H}(\text{CLF5030NIT-4R7}), \ \text{C}_{\text{IN}} = 4.7 \mu \text{F} \times 2(\text{C2012X6S1H475K}) \\ \text{C}_{\text{L}} = 10 \mu \text{F} \times 2(\text{C3216X7R1E106K}) \end{split}$$

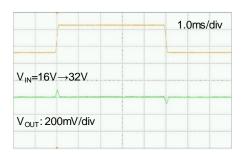
	1.0ms/div
V _{IN} =16V→32V	
V _{OUT} : 200mV/div	V

 $\label{eq:constraint} \begin{array}{l} XC9267B75Cxx, \ f_{OSC} = 1.2MHz \\ V_{IN} = 8V \rightarrow 16V, \ V_{OUT} = 5.0V, \ I_{OUT} = 300mA \end{array}$

	1.0ms/div
V _{IN} =8V→16V	
V _{OUT} : 200mV/div	Y

XC9267B75Cxx、f_{OSC}=1.2MHz V_{IN}=16V→32V, V_{OUT}=5.0V, I_{OUT}=300mA

L=6.8µH(CLF5030NIT-6R8), C_{IN}=4.7µF×2(C2012X6S1H475K) C_L=10µF×2 (C3216X7R1E106K)



■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

(16) Input Transient Response

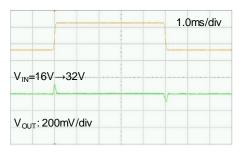
 $\label{eq:constraint} \begin{array}{l} XC9267B75Dxx, \ f_{OSC} = 2.2MHz \\ \mbox{L=2.2} \mu H (CLF5030NIT-2R2), \ C_{1N} = 2.2 \mu F \times 2 (C2012X7R1H225K) \\ \ C_{L} = 10 \mu F \times 2 \ (C3216X7R1E106K) \end{array}$

	1.0ms/div
V _{IN} =8V→16V	
V _{out} : 200mV/div	

 $\begin{array}{l} XC9267B75Dxx, \ f_{OSC}{=}2.2MHz \\ v_{\text{IN}{=}8V \rightarrow 16V, \ V_{OUT}{=}5.0V, \ I_{OUT}{=}300\text{mA} \\ \text{L}{=}3.3\mu\text{H}(\text{CLF5030NIT-3R3}), \ C_{\text{IN}{=}}2.2\mu\text{F}{\times}2(\text{C2012X7R1H225K}) \\ C_{\text{L}{=}10\mu\text{F}{\times}2} \ (\text{C3216X7R1E106K}) \end{array}$

	1.0ms/div
V _{IN} =8V→16V	
V _{out} : 200mV/div	V

 $\begin{array}{l} XC9267B75Dxx, \ f_{OSC}{=}2.2MHz \\ V_{1N}{=}16V{\rightarrow}32V, \ V_{OUT}{=}5.0V, \ I_{OUT}{=}300mA \\ L{=}3.3\mu H(CLF5030NIT{-}3R3), \ C_{1N}{=}2.2\mu F{\times}2(C2012X7R1H225K) \\ C_{L}{=}10\mu F{\times}2 \ (C3216X7R1E106K) \end{array}$



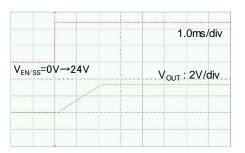
(17) EN/SS Rising Response

 $\begin{array}{l} XC9267B75Cxx, \ f_{OSC} = 1.2MHz \\ v_{\text{IN}} = 12V, \ v_{\text{ENSS}} = 0 \rightarrow 12V, \ v_{\text{OUT}} = 3.3V, \ I_{\text{OUT}} = 300\text{mA} \\ \text{L} = 4.7 \mu \text{H}(\text{CLF5030NIT-4R7}), \ C_{\text{IN}} = 4.7 \mu \text{F} \times 2(\text{C2012X6S1H475K}) \\ C_{\text{L}} = 10 \mu \text{F} \times 2 \ (\text{C3216X7R1E106K}) \end{array}$

	1.0ms/div
V _{EN/SS} =0V→12V	V _{OUT} : 2V/div

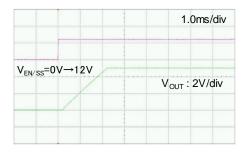
XC9267B75Cxx、f_{OSC}=1.2MHz V_{IN}=24V, V_{ENSS}=0→24V, V_{OUT}=3.3V, I_{OUT}=300mA

L=4.7 μ H(CLF5030NIT-4R7), C_{IN}=4.7 μ F×2(C2012X6S1H475K) C_L=10 μ F×2 (C3216X7R1E106K)



(17) EN/SS Rising Response

 $\begin{array}{l} XC9267B75Cxx, \ f_{OSC} = 1.2MHz \\ v_{\text{IN}} = 12V, \ v_{\text{ENSS}} = 0 \rightarrow 12V, \ v_{\text{OUT}} = 5V, \ I_{\text{OUT}} = 300\text{mA} \\ \text{L} = 6.8 \mu \text{H}(\text{CLF5030NIT-6R8}), \ C_{\text{IN}} = 4.7 \mu \text{F} \times 2(\text{C2012X6S1H475K}) \\ C_{\text{L}} = 10 \mu \text{F} \times 2 \ (\text{C3216X7R1E106K}) \end{array}$



XC9267B75Dxx、f_{OSC}=2.2MHz

 $\label{eq:VIN=12V, V_{ENSS}=0 \to 12V, V_{OUT}=3.3V, I_{OUT}=300mA \\ L=2.2 \mu H (CLF5030NIT-2R2), C_{IN}=2.2 \mu F \times 2 (C2012X7R1H225K) \\ C_L=10 \mu F \times 2 (C3216X7R1E106K) \\ \end{array}$

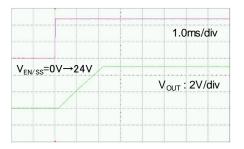
1.0ms/div
V _{OUT} : 2V/div

XC9267B75Dxx、 f_{OSC} =2.2MHz

$$\label{eq:VIN} \begin{split} V_{IN} = & 12V, \ V_{ENSS} = & 0 {\rightarrow} 12V, \ V_{OUT} = & 5V, \ I_{OUT} = & 300 \text{mA} \\ L = & 3.3 \mu \text{H}(\text{CLF5030NIT-3R3}), \ C_{IN} = & 2.2 \mu \text{F} \times & 2(\text{C2012X7R1H225K}) \\ C_L = & 10 \mu \text{F} \times & 2(\text{C3216X7R1E106K}) \end{split}$$

	1.0ms/div
V _{EN/SS} =0V→12V	V _{out} : 2V/div

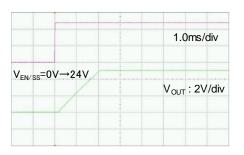
$\begin{array}{l} XC9267B75Cxx, \ f_{OSC} = 1.2MHz \\ v_{\text{IN}} = 24V, \ v_{\text{ENSS}} = 0 {\rightarrow} 24V, \ v_{\text{OUT}} = 5V, \ I_{\text{OUT}} = 300\text{mA} \\ \text{L} = 6.8 \mu\text{H}(\text{CLF5030NIT-6R8}), \ C_{\text{IN}} = 4.7 \mu\text{F} \times 2(\text{C2012X6S1H475K}) \\ C_{\text{L}} = 10 \mu\text{F} \times 2 \ (\text{C3216X7R1E106K}) \end{array}$



XC9267B75Dxx, f_{OSC} =2.2MHz

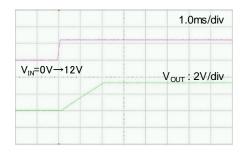
 $V_{\text{IN}}\!\!=\!\!24\text{V}, \ V_{\text{ENSS}}\!\!=\!\!0 \!\!\rightarrow\!\!24\text{V}, \ V_{\text{OUT}}\!\!=\!\!5\text{V}, \ I_{\text{OUT}}\!\!=\!\!300\text{mA}$

L=3.3 μ H(CLF5030NIT-3R3), C_{IN}=2.2 μ F×2(C2012X7R1H225K) C_L=10 μ F×2 (C3216X7R1E106K)



(18) VIN Rising Response

 $\begin{array}{l} XC9267B75Cxx, \ f_{OSC}{=}1.2MHz \\ v_{\text{IN}{=}0}{\rightarrow}12\text{V}, \ v_{\text{ENSS}{=}0}{\rightarrow}12\text{V}, \ v_{\text{OUT}{=}3.3\text{V}, \ I_{\text{OUT}{=}300\text{mA}} \\ \text{L}{=}4.7\mu\text{H}(\text{CLF5030NIT-}4\text{R7}), \ c_{\text{I}{=}}4.7\mu\text{F}{\times}2(\text{C2012X6S1H475K}) \\ c_{\text{L}{=}10\mu\text{F}{\times}2} \ (\text{C3216X7R1E106K}) \end{array}$



XC9267B75Cxx、f_{OSC}=1.2MHz

$$\begin{split} V_{IN}\!\!=\!\!0\!\rightarrow\!12V, \ V_{ENSS}\!=\!\!0\!\rightarrow\!12V, \ V_{OUT}\!=\!\!5V, \ I_{OUT}\!=\!\!300\text{mA}\\ L\!\!=\!\!6.8\mu\text{H}(\text{CLF5030NIT-6R8}), \ C_{IN}\!=\!\!4.7\mu\text{F}\!\times\!2(\text{C2012X6S1H475K})\\ C_L\!\!=\!\!10\mu\text{F}\!\times\!2\ (\text{C3216X7R1E106K}) \end{split}$$

ms/div
2V/div

$\label{eq:constraint} \begin{array}{l} XC9267B75Cxx, \ f_{OSC} = 1.2MHz \\ v_{\text{IN}} = 0 \rightarrow 24 \text{V}, \ v_{\text{ENSS}} = 0 \rightarrow 24 \text{V}, \ v_{\text{OUT}} = 3.3 \text{V}, \ I_{\text{OUT}} = 300 \text{mA} \end{array}$

L=4.7 μ H(CLF5030NIT-4R7), C_{IN}=4.7 μ F×2(C2012X6S1H475K) C_L=10 μ F×2 (C3216X7R1E106K)



XC9267B75Cxx、f_{OSC}=1.2MHz

$$\begin{split} &V_{IN}\!\!=\!\!0\!\rightarrow\!\!24V,\ V_{ENSS}\!\!=\!\!0\!\rightarrow\!\!24V,\ V_{OUT}\!\!=\!\!5V,\ I_{OUT}\!\!=\!\!300\text{mA}\\ &L\!\!=\!\!6.8\mu\text{H}(\text{CLF5030NIT-6R8}),\ C_{IN}\!\!=\!\!4.7\mu\text{F}\!\times\!\!2(\text{C2012X6S1H475K})\\ &C_L\!\!=\!\!10\mu\text{F}\!\times\!\!2(\text{C3216X7R1E106K}) \end{split}$$

V _{OUT} : 2V/div

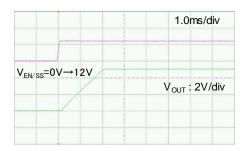
XC9267B75Dxx、f_{OSC}=2.2MHz

$$\begin{split} V_{IN}=&0{\rightarrow}12V,\ V_{ENSS}=&0{\rightarrow}12V,\ V_{OUT}=&3.3V,\ I_{OUT}=&300mA\\ L=&2.2\mu H(CLF5030NIT-2R2),\ C_{IN}=&2.2\mu F\times&2(C2012X7R1H225K)\\ C_{L}=&10\mu F\times&2\ (C3216X7R1E106K) \end{split}$$

V _{OUT} : 2V/div

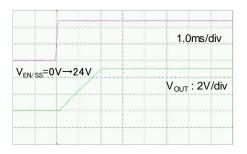
(18) VIN Rising Response

 $\begin{array}{c} XC9267x75D, \ f_{OSC} = 2.2MHz \\ v_{\text{IN}=0 \rightarrow 12V}, \ v_{\text{ENSS}=0 \rightarrow 12V}, \ v_{\text{OUT}} = 5V, \ I_{\text{OUT}} = 300\text{mA} \\ \text{L} = 3.3 \mu\text{H}(\text{CLF5030NIT-3R3N-D}), \ C_{\text{IN}} = 2.2 \mu\text{F} \times 2 (\text{C2012X7R1H225K}) \\ C_{\text{L}} = 10 \mu\text{F} \times 2 \ (\text{C3216X7R1E106K}) \end{array}$



XC9267B75Dxx、 f_{OSC} =2.2MHz

 $\label{eq:VIN} \begin{array}{l} V_{IN}\!\!=\!\!0\!\!\rightarrow\!\!24V, \ V_{ENSS}\!\!=\!\!0\!\!\rightarrow\!\!24V, \ V_{OUT}\!\!=\!\!5V, \ I_{OUT}\!\!=\!\!300\text{mA} \\ L\!\!=\!\!3.3\mu\text{H}(\text{CLF5030NIT-}3\text{R3N-D}), \ C_{IN}\!\!=\!\!2.2\mu\text{F}\!\times\!\!2(\text{C2012X7R1H225K}) \\ C_L\!\!=\!\!10\mu\text{F}\!\times\!2\ (\text{C3216X7R1E106K}) \end{array}$



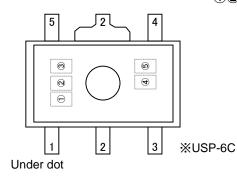
■ PACKAGING INFORMATION

For the latest package information go to, www.torexsemi.com/technical-support/packages

PACKAGE	OUTLIN / LAND PATTERN	THERMAL CHARACTERISTICS		
SOT-89-5	<u>SOT-89-5 PKG</u>	Standard Board	SOT-89-5 Power Dissipation	
		JESD51-7 Board		
USP-6C	USP-6C PKG	Standard Board		
		JESD51-7 Board	USP-6C Power Dissipation	

■MARKING RULE

●SOT-89-5



(1)2) represents product series, products type,

MARK			
	2	- PRODUCT SERIES	
5	1	XC9267B75***-G	
	2	XC9267C75***-G	

●USP-6C(Under dot)

1			Θ] [6
2]	Æ	0][5
3		Ø	ω]	4

$\textcircled{3} \quad \text{represents Oscillation Frequency} \\$

MARK	Oscillation Frequency	PRODUCT SERIES	
Ν	1.2MHz	XC926**75C**-G	
U 2.2MHz		XC926**75D**-G	

(4)(5) represents production lot number

01~09, 0A~0Z, 11~9Z, A1~A9, AA~AZ, B1~ZZ repeated (G, I, J, O, Q, W excluded)* No character inversion used.

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